

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of
Invention

METHOD FOR FORMING DAMASCENE STRUCTURE
UTILIZING PLANARIZING MATERIAL COUPLED WITH
DIFFUSION BARRIER MATERIAL

Confirmation Number:

First Named Applicant: William Wille

Attorney Docket Number: FIS920030024US1

Search string: (6316167 or 20020164877 or 20010036748 or 20020012876).pn.

Certification: This Information Disclosure Statement was submitted under the following conditions, which satisfies the requirement under 37 CFR 1.97(e). The filer certified:

That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
EC	1	6316167	2001-11-13	Angelopoulos, et al.			

US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
EC	1	20020164877	2002-11-07	Catabay, et al.			
I	2	20010036748	2001-11-01	Rutter, Jr., et al.			
✓	3	20020012876	2002-01-31	Angelopoulos, et al.			

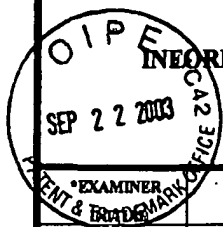
Signature

Eric Chen

1/13/05

Examiner Name

Date

**INFORMATION DISCLOSURE CITATION**

(Use several sheets if necessary)

Docket Number (Optional)

FIS920030024US1

Application Number

10/604,056

Applicant(s)

William Wille, et al.

Filing Date

6/24/03

Group Art Unit

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EC "A High Performance 0.13 um Copper BEOL Technology with Low-K Dielectric" R.D. Goldblatt, et al. Proceedings of the IEEE 2000 International Interconnect Technology Conference, 5-7 June, 2000, pp. 261-263.

EC "A Manufacturable Copper/Low-k SiOC/SiCN Process Technology for 90nm-node High Performance eDRAM", K. Higashi, et al, Proceedings of the IEEE 2002 International Interconnect Technology Conference, 3-5 June 2002, pp. 15-17.

EC "A High Resolution 248 nm Bilayer Resist" Qinghuang Lin, et al., Proc. SPIE - Int. Soc. Opt. Eng. (USA), vol. 3678, pt. 1-2, pp. 241-50.

EC "Surface treatment validation of inorganic BARC on 0.25 um Non Volatile Memory technology", Y. Trouilleret al. Microelectronic Engineering 46 (1999), pp. 47-50.

EC "Effects of Crosslinking Agent on Lithographic Performance of Negative-Tone Resists Based on Poly (p-hydroxystyrene)", Qinghuang Lin, et al. Proc. SPIE - Int. Soc. Opt. Eng. (USA), vol 3049, pp. 974-87.

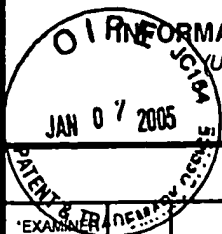
EC Patent Application, Serial Number 09/256,034, dated 2/23/99, Inventors M. Angelopoulos, et al. Entitled Multilayered Resist System Using Tuned Polymer Films as Underlayers and Methods of Fabrication Thereof.

EXAMINER

DATE CONSIDERED

1/19/05

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



OFFICE INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.
FIS920030024US1SERIAL NO.
10/604,056FILING
6/24/03

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EC	6,720,256	4/13/2004	Wu, et al.			
EC	2004/0018721	1/29/2004	Kim, et al.			
EC	6,365,529	4/2/2002	Hussein, et al.			
EC	5,883,006	3/16/1999	Iba			
EC	6,426,298	7/30/2002	Chen, et al.			
EC	2002/0058204	5/16/2002	Khojasteh, et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
EC	JP2000208620A	2000-07-28	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

Eric Chan

DATE CONSIDERED

1/26/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.